

RGTV00TK65

650V 50A Field Stop Trench IGBT

V _{CES}	650V
I _{C (100°C)}	26A
V _{CE(sat) (Typ.)}	1.5V@I _C =50A
P _D	94W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching & Low Switching Loss
- 3) Short Circuit Withstand Time 2µs
- 4) Pb free Lead Plating; RoHS Compliant

Applications

Solar Inverter

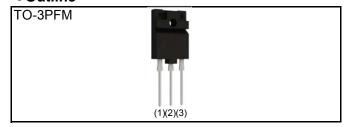
UPS

Welding

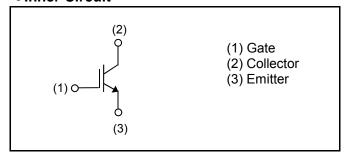
ΙH

PFC

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Typo	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTV00TK65

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
T _C = 25°C		I _C	45	А
Collector Current	T _C = 100°C	I _C	26	А
Pulsed Collector Current		I _{CP} *1	200	А
$T_C = 25^{\circ}C$		P _D	94	W
Power Dissipation $T_C = 100^{\circ}C$		P _D	47	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax}.

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	1	-	1.59	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r ai ai iletei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	1	-	V
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	1	1	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	V _{CE} = 5V, I _C = 34.3mA	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 50A$, $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.5 1.85	1.9 -	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Davamatar	Cymphol	Conditions		Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input Capacitance	C _{ies}	V _{CE} = 30V	-	2890	-	
Output Capacitance	C _{oes}	V _{GE} = 0V	-	116	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	48	-	
Total Gate Charge	Q _g	V _{CE} = 400V	-	104	-	
Gate - Emitter Charge	Q_{ge}	I _C = 50A	-	21	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	37	-	
Turn - on Delay Time	t _{d(on)}	I _C = 50A, V _{CC} = 400V	-	41	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	20	-	
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	142	-	ns
Fall Time	t _f	Inductive Load	-	38	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	1.17	-	m l
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.94	-	mJ
Turn - on Delay Time	t _{d(on)}	I _C = 50A, V _{CC} = 400V	-	39	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	23	-	
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	167	-	ns
Fall Time	t _f	Inductive Load	-	80	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	1.25	-	m l
Turn - off Switching Loss	E _{off}	reverse recovery	-	1.28	-	mJ
		I _C = 200A, V _{CC} = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FU	LL SQUA	RE	-
		$R_G = 100\Omega, T_j = 175^{\circ}C$				
		$V_{CC} \le 360V$				
Short Circuit Withstand Time	t _{sc}	V _{GE} = 15V	2	-	-	μs
		T _j = 25°C				

Fig.1 Power Dissipation vs. Case Temperature

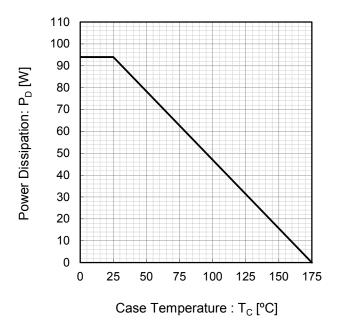


Fig.2 Collector Current vs. Case Temperature

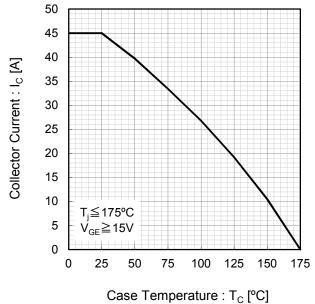


Fig.3 Forward Bias Safe Operating Area

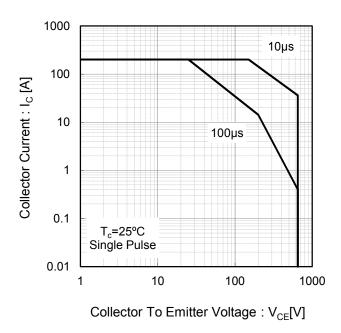


Fig.4 Reverse Bias Safe Operating Area

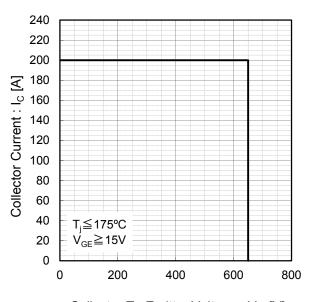


Fig.5 Typical Output Characteristics

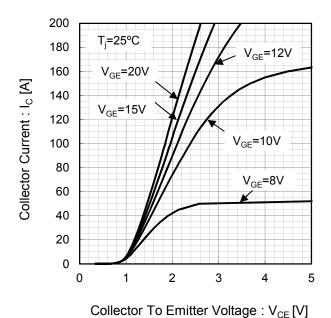
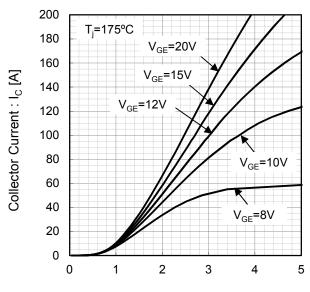


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage: V_{CE}[V]

Fig.7 Typical Transfer Characteristics

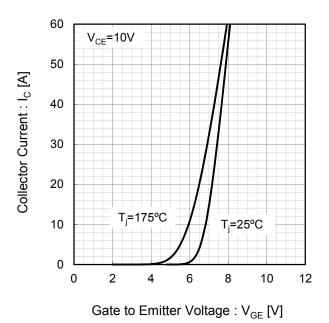


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature

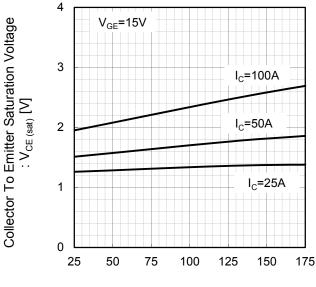


Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

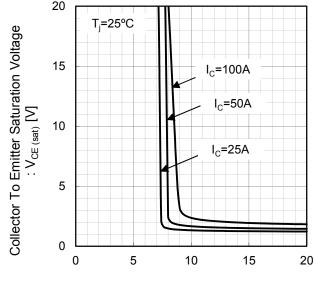
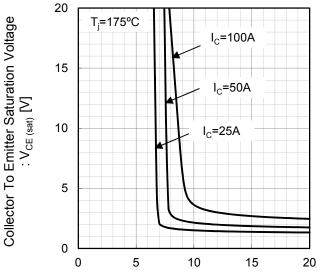


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate to Emitter Voltage : V_{GE} [V]

Gate to Emitter Voltage : V_{GE} [V]

Fig.11 Typical Switching Time vs. Collector Current

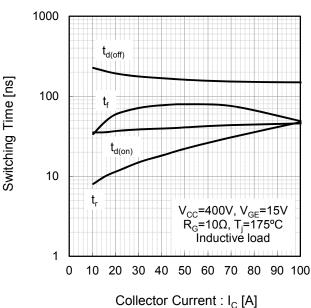
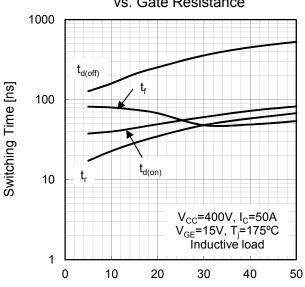


Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance : R_G [Ω]

Fig.13 Typical Switching Energy Losses vs. Collector Current

10 E_{off} E_{on} V_{CC} =400V, V_{GE} =15V R_{G} =10 Ω , T_{j} =175°C

Inductive load

0.01

Collector Current : I_{C} [A]

Fig.14 Typical Switching Energy Losses vs. Gate Resistance 10 Switching Energy Losses [mJ] $\mathsf{E}_{\mathsf{off}}$ 1 E_{on} 0.1 V_{CC}=400V, I_C=50A V_{GE}=15V, T_j=175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance : $R_G [\Omega]$

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V_{GE}=0V =25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : $V_{CE}[V]$

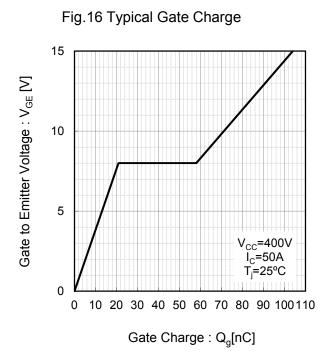
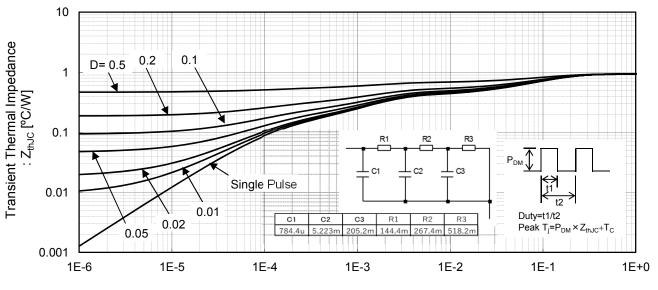


Fig.17 Typical IGBT Transient Thermal Impedance



Pulse Width: t1[s]

•Inductive Load Switching Circuit and Waveform

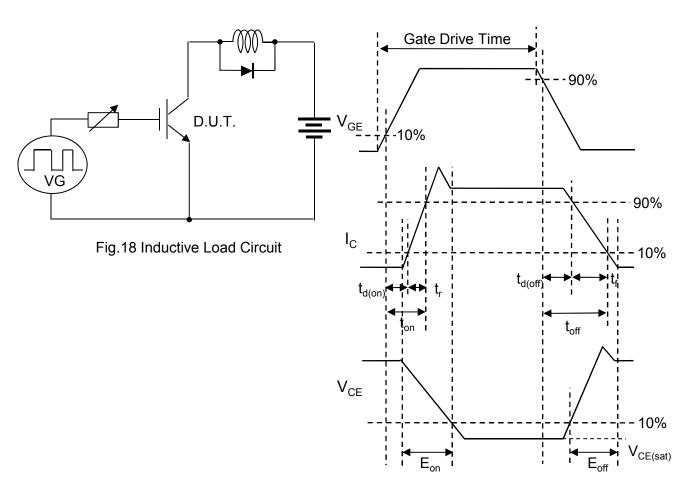


Fig.19 Inductive Load Waveform

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RGTV00TK65 - Web Page

Distribution Inventory

Part Number	RGTV00TK65
Package	TO-3PFM
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes